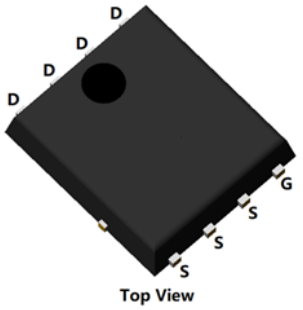
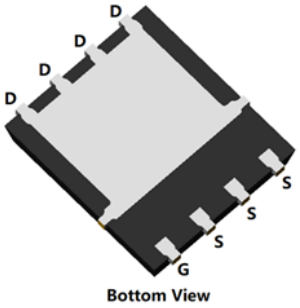
# N-Channel Enhancement Mode Field Effect Transistor

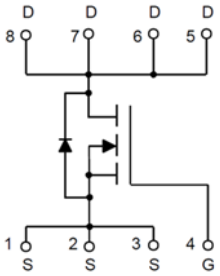



Top View




Bottom View

PDFN5060-8L




## Product Summary

- $V_{DS}$ 40 V
- $I_D$ 100 A
- $R_{DS(ON)}$( at $V_{GS}$=10V) ＜3.5 mohm
- $R_{DS(ON)}$( at $V_{GS}$=4.5V) ＜4.8 mohm
- 100% EAS Tested
- 100% ▽$V_{DS}$ Tested

## General Description

- Trench Power LV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

## Applications

- DC-DC Converters
- Power management functions
- Backlighting

## ■ Absolute Maximum Ratings ($T_A$=25℃unless otherwise noted)

| Parameter | | Symbol | Limit | Unit |
|---|---|---|---|---|
| Drain-source Voltage | | $V_{DS}$ | 40 | V |
| Gate-source Voltage | | $V_{GS}$ | ±20 | V |
| Drain Current | $T_C$=25℃ | $I_D$ | 100 | A |
| | $T_C$=100℃ | | 63 | |
| Pulsed Drain Current [A] | | $I_{DM}$ | 360 | A |
| Total Power Dissipation @ $T_C$=25℃ [B] | | $P_D$ | 83 | W |
| Total Power Dissipation @ $T_C$=100℃ [B] | | $P_D$ | 30 | W |
| Total Power Dissipation @ $T_A$=25℃ [C] | | $P_D$ | 6.2 | W |
| Single Pulse Avalanche Energy [D] | | $E_{AS}$ | 400 | mJ |
| Thermal Resistance Junction-to-Case | | $R_{\theta JC}$ | 1.67 | ℃/ W |
| Thermal Resistance Junction-to-Ambient | | $R_{\theta JA}$ | 20 | ℃/ W |
| Junction and Storage Temperature Range | | $T_J$ ,$T_{STG}$ | -55～+150 | ℃ |

## ■ Ordering Information (Example)

| PREFERED P/N | PACKING CODE | Marking | MINIMUM PACKAGE(pcs) | INNER BOX QUANTITY(pcs) | OUTER CARTON QUANTITY(pcs) | DELIVERY MODE |
|---|---|---|---|---|---|---|
| G100N04A | F1 | G100N04A | 5000 | 10000 | 100000 | 13“ reel |

## ■ Electrical Characteristics ($T_J$=25℃ unless otherwise noted)

| Parameter | Symbol | Conditions | Min | Typ | Max | Units |
|---|---|---|---|---|---|---|
| **Static Parameter** | | | | | | |
| Drain-Source Breakdown Voltage | $BV_{DSS}$ | $V_{GS}$= 0V, $I_D$=250μA | 40 | | | V |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$=40V,$V_{GS}$=0V | | | 1 | μA |
| Gate-Body Leakage Current | $I_{GSS}$ | $V_{GS}$= ±20V, $V_{DS}$=0V | | | ±100 | nA |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$= $V_{GS}$, $I_D$=250μA | 1.0 | 1.5 | 2.5 | V |
| Static Drain-Source On-Resistance | $R_{DS(ON)}$ | $V_{GS}$= 10V, $I_D$=20A | | 2.8 | 3.5 | mΩ |
| | | $V_{GS}$= 4.5V, $I_D$=20A | | 4.0 | 4.8 | |
| Diode Forward Voltage | $V_{SD}$ | $I_S$=20A,$V_{GS}$=0V | | 0.80 | 1.2 | V |
| Maximum Body-Diode Continuous Current | $I_S$ | | | | 100 | A |
| Gate resistance | Rg | f=1 MHz | | 3.5 | | Ω |
| **Dynamic Parameters** | | | | | | |
| Input Capacitance | $C_{iss}$ | $V_{DS}$=20V,$V_{GS}$=0V,f=1MHZ | | 4645 | | pF |
| Output Capacitance | $C_{oss}$ | | | 436 | | |
| Reverse Transfer Capacitance | $C_{rss}$ | | | 360 | | |
| **Switching Parameters** | | | | | | |
| Total Gate Charge | $Q_g$(10V) | $V_{GS}$=10V,$V_{DS}$=20V,$I_D$=20A | | 102 | | nC |
| Total Gate Charge | $Q_g$(4.5V) | | | 49 | | |
| Gate-Source Charge | $Q_{gs}$ | | | 15.8 | | |
| Gate-Drain Charge | $Q_{gd}$ | | | 21.9 | | |
| Reverse Recovery Charge | $Q_{rr}$ | $I_F$=20A, di/dt=100A/us | | 7.4 | | |
| Reverse Recovery Time | $t_{rr}$ | | | 22.3 | | ns |
| Turn-on Delay Time | $t_{D(on)}$ | $V_{GS}$=10V, $V_{DD}$=20V , $I_D$=20A $R_{GEN}$=3Ω | | 12 | | |
| Turn-on Rise Time | $t_r$ | | | 54 | | |
| Turn-off Delay Time | $t_{D(off)}$ | | | 120 | | |
| Turn-off fall Time | $t_f$ | | | 80 | | |

A. Pulse Test: Pulse Width≤300us,Duty cycle ≤2%.
B. The power dissipation $P_D$ is based on $T_{J(MAX)}$=150℃, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. The value of $R_{\theta JA}$ is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with $T_A$ =25℃.
D. $T_j$=25℃, $V_{DD}$=40V, $V_G$=10V, L=2mH.

## ■ Typical Performance Characteristics

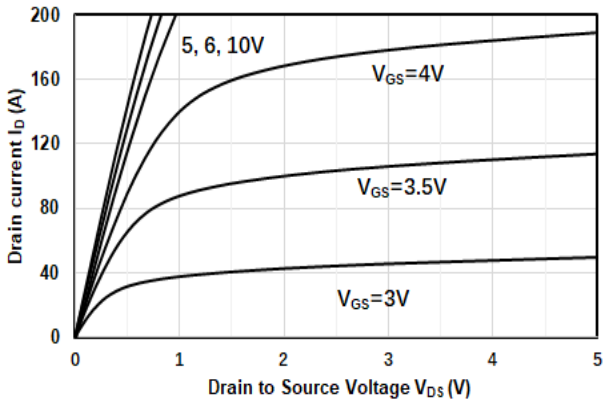



Figure1. Output Characteristics

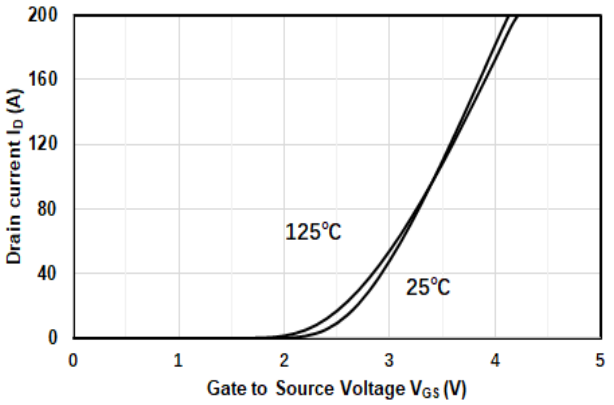



Figure2. Transfer Characteristics

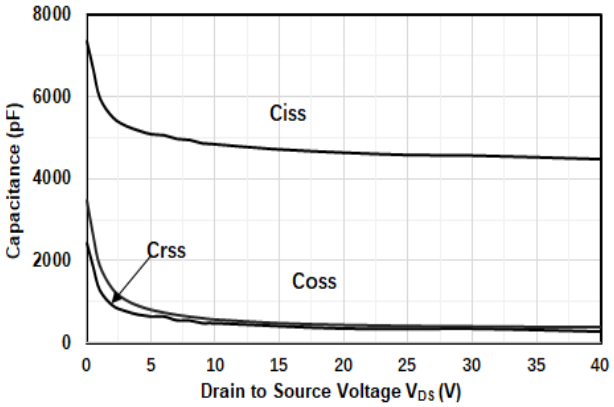



Figure3. Capacitance Characteristics

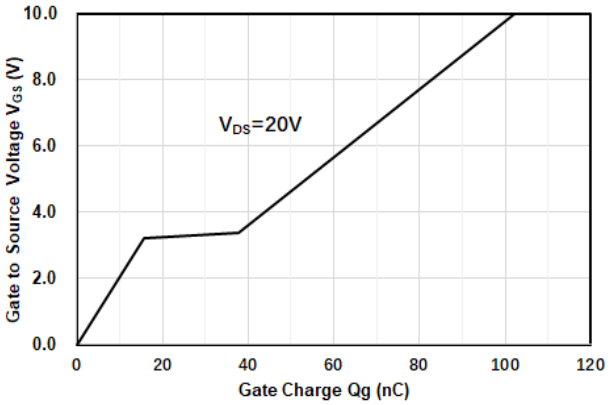



Figure4. Gate Charge

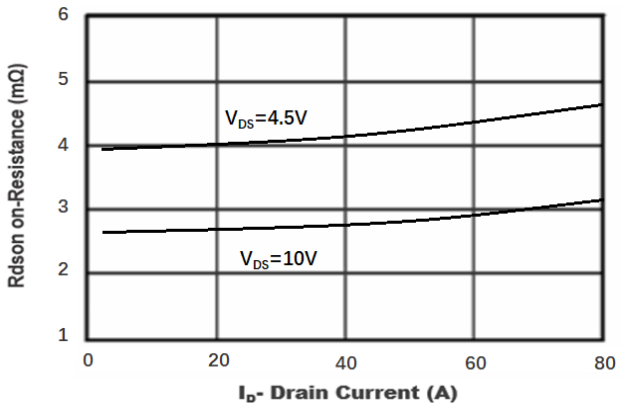



Figure5. Drain-Source on Resistance

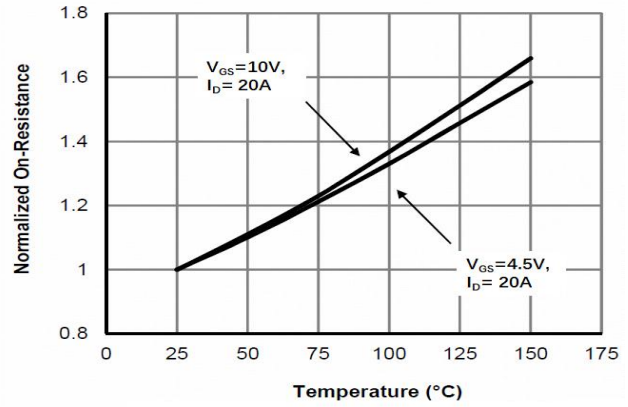



Figure6. Drain-Source on Resistance

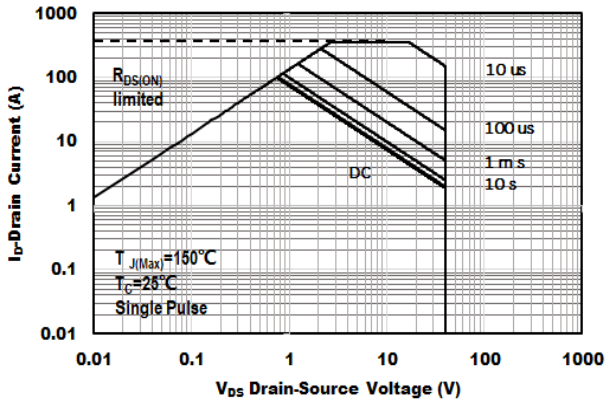



Figure7. Safe Operation Area

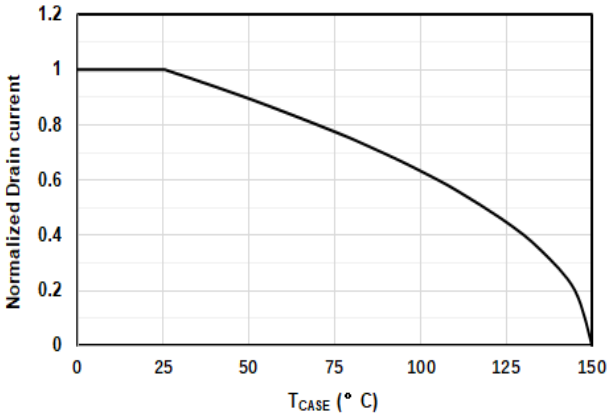



Figure8. Drain current vs. Case Temperature

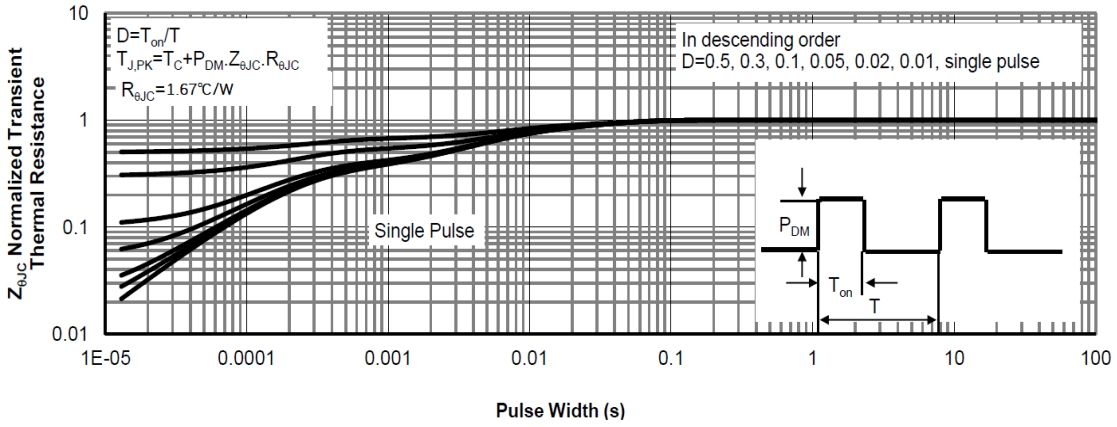
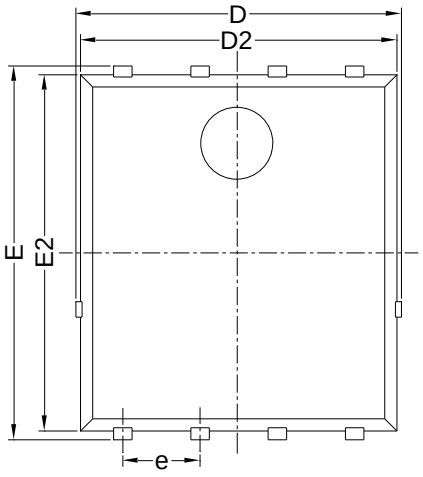
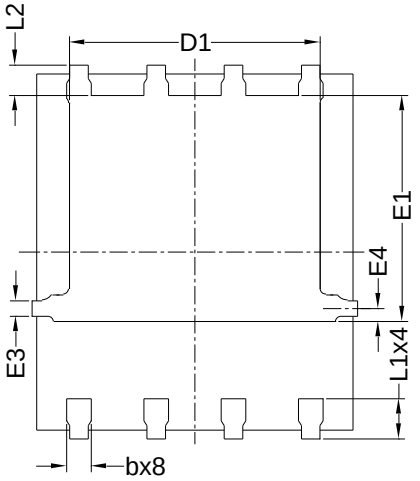



Figure9. Normalized Maximum Transient Thermal Impedance

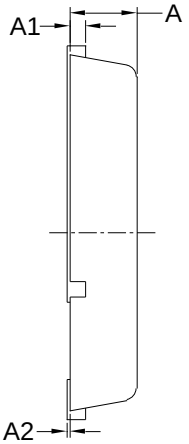
## ■ PDFN5060-8L-B-1.1MM Package information



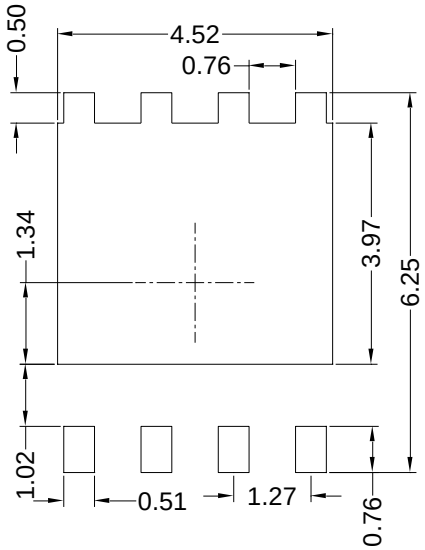

Top View
正面视图




Bottom View
背面视图




Side View
侧面视图




Suggested Solder Pad Layout
Top View

| SYMBOL | MILLIMETER | | |
|---|---|---|---|
| | MIN | NOM | MAX |
| D | 5.15 | 5.35 | 5.55 |
| E | 5.95 | 6.15 | 6.35 |
| A | 1.00 | 1.10 | 1.20 |
| A1 | | 0.254 BSC | |
| A2 | | | 0.10 |
| D1 | 3.92 | 4.12 | 4.32 |
| E1 | 3.52 | 3.72 | 3.92 |
| D2 | 5.00 | 5.20 | 5.40 |
| E2 | 5.66 | 5.86 | 6.06 |
| E3 | | 0.254 REF | |
| E4 | | 0.21 REF | |
| L1 | 0.56 | 0.66 | 0.76 |
| L2 | | 0.50 BSC | |
| b | 0.31 | 0.41 | 0.51 |
| e | | 1.27 BSC | |

Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.10mm.
3.The pad layout is for reference purposes only.

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